

Design & Simulate 4 Ex1.6  
ECE2204 CRN:82929

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August 31, 2018

## Problem 4.6.a.1:

### Design

Consider a silicon pn junction at  $T = 300K$  with a donor doping concentration of  $N_d = 10^{14}cm^{-3}$ , and at  $V_R = 3V$  the junction capacitance is  $C_j = 0.245pF$ . Assume that the Boltzmann constant is  $k = 86 \times 10^{-6}eV/K$ , the electron charge is  $e = 1.6 \times 10^{-19}C$ ,  $n_i = 2.3 \times 10^{10}cm^{-3}$  and  $C_{j0} = 0.7pF$ . Assume  $e$  is the exponential. Find the acceptor doping concentration  $N_a$ .

$$V_{bi} = \frac{kT}{e} \ln\left(\frac{N_a N_d}{n_i^2}\right) \implies N_a = \frac{n_i^2}{N_d} e^{\left(\frac{e \times V_{bi}}{kT}\right)} \quad (1)$$

$$C_j = C_{j0} \left(1 + \frac{V_R}{V_{bi}}\right)^{-1/2} \implies V_{bi} = \frac{V_R}{\left(\frac{C_j}{C_{j0}}\right)^{-2} - 1} \quad (2)$$

$$V_{bi} = \frac{3V}{\left(\frac{0.245pF}{0.7pF}\right)^{-2} - 1} = 0.42V \quad (3)$$

$$N_a = \frac{(2.3 \times 10^{10}cm^{-3})^2}{10^{14}cm^{-3}} e^{\left(\frac{1.6 \times 10^{-19}C \times 0.42V}{300K \times 86 \times 10^{-6}eV/K}\right)} = 6.078 \times 10^{13}cm^{-3} \quad (4)$$

The acceptor doping concentration is  $N_a = 6.078 \times 10^{13}cm^{-3}$ .

### Validation

I was not able to get LTSpice to generate a validation simulation with  $N_a$  as my dependent value. As a result there is no validation simulation.

**Note to grader:** If you know how to get LTSpice to simulate with  $N_a$  as the dependent variable and  $V_R$  as the driving independent variable, I would be very appreciative if you could leave me a comment as to how. Despite being generally decent with LTSpice I could not make it work this time around.

## Problem 4.6.b.1:

Derived from 1.23 by changing values.

### Design

The zero-biased junction capacitance of a silicon pn junction is  $C_{j0} = 0.5pF$ . The doping concentrations are  $N_a = 1.2 \times 10^{16}cm^{-3}$  and  $N_d = 5 \times 10^{15}cm^{-3}$ . Assume  $n_i = 1.5 \times 10^{10}cm^{-3}$ . Determine the junction capacitance at  $V_R = 2V$ .

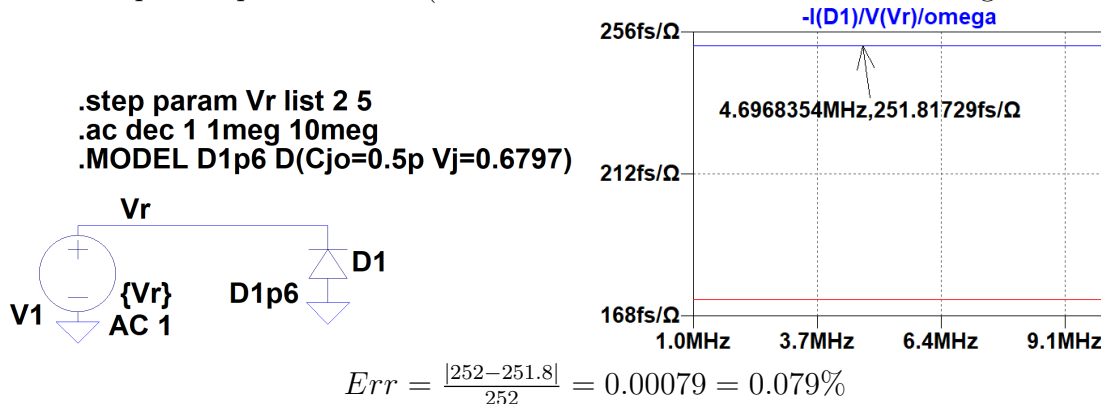
$$V_{bi} = \frac{300K \times 86 \times 10^{-6} eV/K}{1.6 \times 10^{-19} C} \ln\left(\frac{1.2 \times 10^{16} cm^{-3} \times 5 \times 10^{15} cm^{-3}}{(1.5 \times 10^{10} cm^{-3})^2}\right) = 0.6797V \quad (5)$$

$$C_j = 0.5pF \left(1 + \frac{2V}{0.6797V}\right)^{-1/2} = 0.252pF \quad (6)$$

The junction capacitance at  $V_R = 2V$  is  $C_j = 0.252pF$

### Validation

LTSpice Implementation (accurate with  $< 1\%$  deviation from design result)



This assignment demonstrates an understanding of basic pn junction theory, the equations, and derivations necessary to solve for parameters essential to the function of pn junctions.

*I have neither given nor received unauthorized assistance on this assignment.*